

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

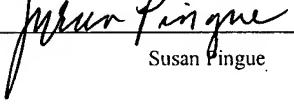
Application No. : CONTINUATION OF 09/916,555
Applicant : Chih Hsin Wang et al.
Filed : HEREWITH
TC/A.U. : 2814
Examiner : M. D. Pizarro-Crespo
Title : A SEMICONDUCTOR MEMORY ARRAY OF FLOATING
GATE MEMORY CELLS WITH LOW RESISTANCE SOURCE
REGIONS AND HIGH SOURCE COUPLING
(as amended)

Docket No. : 2102397-911401
Customer No. : 26379

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as EXPRESS MAIL (EV 302278047 US) in an envelope addressed to Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on October 20, 2003.

GRAY CARY WARE & FREIDENRICH Date: 10/20/03

By: 
Susan Pingue

PRELIMINARY AMENDMENT

Sir:

Please preliminarily amend the above identified application as follows:

Amendments to the Specification begin on page 2 of this paper.

Amendments to the Claims are reflected in the listing of claims which begins on page 4 of this paper.

Remarks/Arguments begin on page 8 of this paper.